

L Number	Hits	Search Text	DB	Time stamp
1	6	"5063342" and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 11:48
3	0	divid\$3 with plurality adj (factors or constants or ratios) and (374/178 or 374/183).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 11:49
2	34	divid\$3 with plurality adj (factors or constants or ratios)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 11:49
4	0	divid\$3 with plurality adj (factors or constants or ratios) and semiconductor same temperture	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 11:50

L Number	Hits	Search Text	DB	Time stamp
1	521	(374/183).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:23
2	23	(second or pair) adj semiconductor and 374/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:23
3	6	(second or pair) adj semiconductor and 374/\$.ccls. and current adj source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:28
4	1560	bipolar adj transistor and darlington	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:54
5	9	("4122719"   "4161880"   "4210024"   "4298947"   "4403296"   "4455095"   "4481596"   "4532601"   "5139858").PN.	USPAT	2003/08/04 08:31
6	0	5224777.URPN.	USPAT	2003/08/04 08:31
7	1213	semiconductor and voltage with ratio with temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:40
8	649	(bipolar adj transistor and darlington) and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:54
9	1767	semiconductor with temperature and current and ratio with voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:47
14	39	aslan.in. and diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:50
13	21	(bipolar adj transistor and darlington) and (semiconductor with temperature and current and ratio with voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:52
16	0	(bipolar adj transistor and darlington) and 374/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:54
17	90	bipolar adj transistor and 374/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:54
19	5	("5195827"   "5453682"   "5993060"   "6008685"   "6332710").PN.	USPAT	2003/08/04 08:56
20	0	6554469.URPN.	USPAT	2003/08/04 08:56
21	0	6225851.URPN.	USPAT	2003/08/04 08:57

22	8	("3825778" "4331888" "5039878" "5159520" "5195827" "5686858"	USPAT	2003/08/04 08:57
18	50	"5982221" "6019058").PN. darlington and 374/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 09:02
10	106	semiconductor with temperature and different adj current and ratio with voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 09:09
23	0	6255891.URPN.	USPAT	2003/08/04 09:11
24	2	("5063342" "5583397").PN.	USPAT	2003/08/04 09:11
25	13	5063342.URPN.	USPAT	2003/08/04 09:12
26	3	("4287439" "4751404" "4935690").PN.	USPAT	2003/08/04 09:12
27	4	("5100829" "5195827" "5349336" "5401099").PN.	USPAT	2003/08/04 09:13
28	2	6149299.URPN.	USPAT	2003/08/04 09:13
12	408	semiconductor with temperature and current and ratio with voltage with temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 09:16
29	121	semiconductor with temperature and current and ratio with voltage same converter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 09:31
30	185	semiconductor with temperature and current and divid\$3 with voltage same converter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 09:31
-	300	(374/178).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/04 08:21
-	61	((374/178).CCLS.) AND divid\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:08
-	76	((374/178).CCLS.) AND RATIO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 15:09